

IN THE CLAIMS:

Kindly cancel claims 1-9 and add new claims 10-37 as shown in the following listing of claims, which replaces all previous versions and listings of claims in the captioned application.

1. - 9. (canceled).

10. (new) A sample correction device comprising: a sample stage for supporting thereon a sample; a first charged particle beam lens barrel for emitting a first charged particle beam for scanning across the sample and correcting a shape defect in the sample by etching or deposition; and first transmitted beam detecting means for detecting a first transmitted beam comprised of the first charged particle beam penetrating through the sample when the sample is supported on the sample stage and is being irradiated by the first charged particle beam.

11. (new) A sample correction device according to claim 10; wherein the sample comprises a fine stencil structure.

12. (new) A sample correction device according to claim 10; wherein the sample comprises an electron beam exposure mask.

13. (new) A sample correction device according to claim 10; wherein the first charged particle beam lens barrel is provided over a first side of the sample stage.

14. (new) A sample correction device according to claim 13; wherein the first transmitted beam detecting means is provided under a second side of the sample stage opposite the first side.

15. (new) A sample correction device according to claim 10; wherein the sample stage has a hole therethrough over which the sample is positioned.

16. (new) A sample correction device according to claim 10; wherein the first transmitted beam detecting means comprises an absorbed current detector which is disposable in a path of the first transmitted beam to generate a current in response thereto, and a current meter for measuring the current.

17. (new) A sample correction device according to claim 16; wherein the absorbed current detector is removably disposable in the path of the first transmitted beam.

18. (new) A sample correction device according to claim 10; wherein the first transmitted beam detecting means comprises a beam target which is disposable in a path of the

first transmitted beam for emitting secondary charged particles in response to irradiation by the first transmitted beam, and a secondary charged particle detector for detecting the secondary charged particles emitted by the beam target.

19. (new) A sample correction device according to claim 10; wherein the first charged particle beam lens barrel comprises a focused ion beam lens barrel.

20. (new) A sample correction device according to claim 19; wherein the focused ion beam lens barrel is provided over a first side of the sample stage, and the first transmitted beam detecting means is disposable in a path of the first transmitted beam.

21. (new) A sample correction device according to claim 20; wherein the first transmitted beam detecting means is provided under a second side of the sample stage opposite the first side.

22. (new) A sample correction device according to claim 10; wherein the first charged particle beam lens barrel is provided over a first side of the sample stage; and further comprising a second charged particle beam lens barrel provided under a second side of the sample stage opposite the first side for emitting a second charged particle beam; and second

transmitted beam detecting means for detecting a second transmitted beam comprised of the second charged particle beam penetrating through the sample when the sample is supported on the sample stage and is being irradiated by the second charged particle beam.

23. (new) A sample correction device according to claim 22; wherein the second transmitted beam detecting means comprises an absorbed current detector which is disposable in a path of the second transmitted beam for generating a current in response thereto, and a current meter for measuring the current.

24. (new) A sample correction device according to claim 23; wherein the absorbed current detector is removably disposable in the path of the second transmitted beam.

25. (new) A sample correction device according to claim 22; wherein at least one of the first and second transmitted beam detecting means comprises an absorbed current detector which also functions as a beam target for emitting secondary electrons when a position of the absorbed current detector is changed relative to the first or second charged particle beam.

26. (new) A sample correction device according to claim 22; wherein the second transmitted beam detecting means comprises a beam target which is disposable in a path of the second transmitted beam to emit secondary charged particles in response thereto, and a secondary charged particle detector for detecting the secondary charged particles emitted by the beam target.

27. (new) A sample correction device according to claim 22; wherein the first charged particle beam lens barrel comprises a focused ion beam lens barrel, and the second charged particle beam lens barrel comprises an electron beam lens barrel.

28. (new) A sample correction device according to claim 27; wherein the first transmitted beam detecting means comprises a first absorbed current detector which is removably disposable under the second side of the sample stage in a path of the first transmitted beam and a path of the second charged particle beam for generating a first current in response to irradiation with the first transmitted beam, and a current meter for measuring the first current, and the second transmitted beam detecting means comprises a second absorbed current detector which is removably disposable over the first side of the sample stage in a path of the second transmitted

beam and a path of the first charged particle beam for generating a second current in response to irradiation with the second transmitted beam, and a current meter for measuring the second current.

29. (new) A sample correction device according to claim 27; wherein the first transmitted beam detecting means comprises a first beam target which is removably disposable under the second side of the sample stage in a path of the first transmitted beam for emitting secondary charged particles in response to irradiation with the first transmitted beam, and a secondary charged particle detector for detecting the secondary charged particles emitted by the first beam target, and the second transmitted beam detecting means comprises a second beam target which is removably disposable over the first side of the sample stage in a path of the second transmitted beam for emitting secondary charged particles in response to irradiation with the second transmitted beam, and a secondary charged particle detector for detecting the secondary charged particles emitted by the second beam target.

30. (new) A sample correction device according to claim 10; further comprising a scanning transmission electron microscope lens barrel for irradiating the sample with a

primary electron beam; and transmitted electron beam detecting means for detecting a transmitted electron beam comprised of the primary electron beam penetrating through the sample while the sample is being irradiated by the primary electron beam.

31. (new) A sample correction device according to claim 30; wherein the transmitted electron beam detecting means comprises one or more lenses for enlarging the transmitted electron beam, and a projection plate onto which the enlarged electron beam is projected.

32. (new) A sample correction device according to claim 10; further comprising a scanning electron microscope lens barrel for irradiating the sample with a primary electron beam that penetrates through the sample.

33. (new) A sample correcting device according to claim 32; wherein the first charged particle beam lens barrel and the scanning electron microscope lens barrel are provided on opposite sides of the sample stage; and further comprising second transmitted beam detecting means provided between the sample stage and the first charged particle beam lens barrel for detecting a second transmitted electron beam comprised of the primary electron beam penetrating through the sample while being irradiated by the primary electron beam; wherein the

first and second transmitted beam detecting means are each alternately retracted when not in use so as not to obstruct beam irradiation by an unused one of the lens barrels.

34. (new) A sample correction device according to claim 33; wherein at least one of the first and second transmitted beam detecting means comprises an absorbed current detector which also functions as a beam target for emitting secondary electrons when a position of the absorbed current detector is changed relative to the charged particle beam or the electron beam.

35. (new) A sample correction device according to claim 33; wherein at least one of the first and second transmitted beam detecting means comprises a movable absorbed current detector which detects an absorbed current in a first position, functions as a beam target for emitting secondary electrons in a second position, and does not function as an absorbed current detector or a beam target in a third position in which it is retracted so as not to obstruct beam irradiation from an unused one of the lens barrels.

36. (new) A fine stencil structure correction device comprising: a sample stage for supporting thereon a fine stencil structure; a focused ion beam lens barrel disposed over the sample stage for emitting a focused ion beam for scanning across the fine stencil structure and correcting

a shape defect in the fine stencil structure by etching or deposition; first transmitted beam detecting means for detecting a first transmitted beam comprised of the focused ion beam penetrating through the fine stencil structure when the fine stencil structure is supported on the sample stage and is being irradiated by the focused ion beam; an electron beam lens barrel disposed under the sample stage for emitting an electron beam for scanning across the fine stencil structure for observing the fine stencil structure; and second transmitted beam detecting means for detecting a second transmitted beam comprised of the electron beam penetrating through the fine stencil structure when the fine stencil structure is supported on the sample stage and is being irradiated by the electron beam.

37. (new) A sample correction device according to claim 36; wherein each of the first and second transmitted beam detecting means comprises one of an absorbed current detector and a beam target which is removably disposable in a path of the first and second transmitted beams to generate a current in response thereto.